TOSHIBA Intelligent Power Module Silicon N Channel IGBT

MIG300J101H

High Power Switching Applications Motor Control Applications

• Integrates inverter power circuits & control circuits (IGBT drive units, protection units for over-current, under-voltage & over temperature) in one package.

The electrodes are isolated from case.

High speed type IGBT : $V_{CE (sat)} = 2.5V (max)$

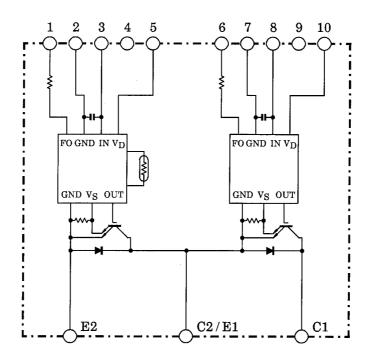
 $t_{off} = 2.6 \mu s \text{ (max)}$

 $t_{rr} = 0.15 \mu s \text{ (max)}$

Package dimensions : TOSHIBA 2-121A1A

Weight : 520g

Equivalent Circuit



- 1. FO (L)
- 2. GND (L)
- 3. IN (L)
- 4. Open

- 6. FO (H)
- 7. GND (H)
- 8. IN (H)

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- 9. Open
- $\begin{array}{cc} 5. \ \mathrm{V_D} \ (\mathrm{L}) \\ 10.\mathrm{V_D} \ (\mathrm{H}) \end{array}$

Maximum Ratings ($T_j = 25$ °C)

Stage	Characteristic	Condition	Symbol	Ratings	Unit
Inverter	Supply voltage	P-N power terminal	V _{CC}	450	V
	Collector-emitter voltage	_	V _{CES}	600	V
	Collector current	Tc = 25°C, DC	Ic	300	Α
	Forward current	Tc = 25°C, DC	lF	300	Α
	Collector power dissipation	Tc = 25°C	PC	1200	W
	Junction temperature	_	Tj	150	°C
Control	Control supply voltage	V _D -GND terminal	V _D	20	V
	Input voltage	IN-GND terminal	V _{IN}	20	V
	Fault output voltage	FO-GND (L) terminal	V _{FO}	20	V
	Fault output current	FO sink current	I _{FO}	14	mA
Module	Operating temperature	_	T _C	-20~+100	°C
	Storage temperature range	_	T _{stg}	-40~+125	°C
	Isolation voltage	AC 1 minute,	V _{ISO}	2500	V
	Screw torque	M6	_	3	Nm

Electrical Characteristics ($T_j = 25$ °C)

a. Inverter Stage

Characteristic	Symbol	Test Condition		Min	Тур.	Max	Unit
Collector cut-off current	lory	V _{CE} = 600V	T _j = 25°C	_	_	2	mA
Collector cut on current	I_{CEX} $V_{CE} = 600V$ T_j	T _j = 125°C	_	_	40	IIIA	
Collector-emitter saturation voltage	V	$V_D = 15V, I_C = 300A$ $V_{IN} = 3V \rightarrow 0V$	T _j = 25°C	_	2.0	2.5	V
Conector-ennitier saturation voltage	V _{CE} (sat)		T _j = 125°C	_	2.0	_	V
Forward voltage	V _F	I _F = 300A		_	2.1	2.7	V
	t _{on}			1.1	1.8	2.5	
	t _{c (on)}	V _{CC} = 300V, I _C = 300A		_	0.8	1.2	
Switching time	t _{rr}	V _D = 15V, V _{IN} = 3V ↔ Inductive load	0V	_	0.08	0.15	μs
	t _{off}		(Note 1)	_	1.9	2.6	
	t _{c (off)}			_	0.3	0.6	



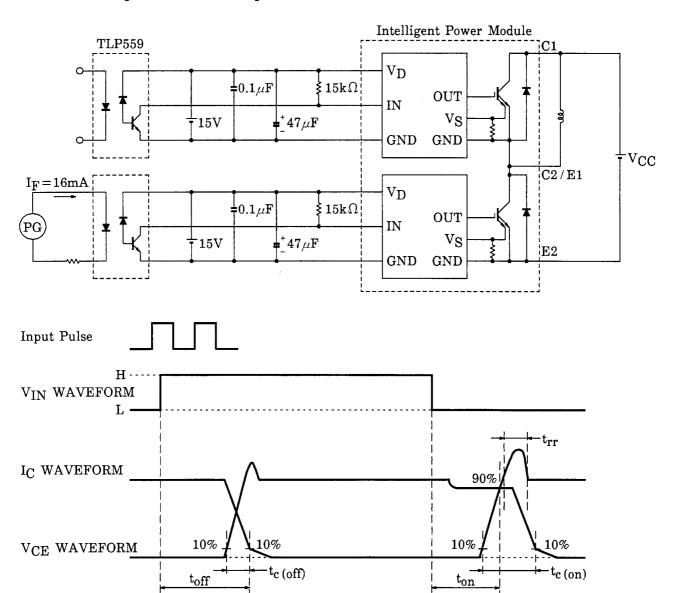
b. Control Stage

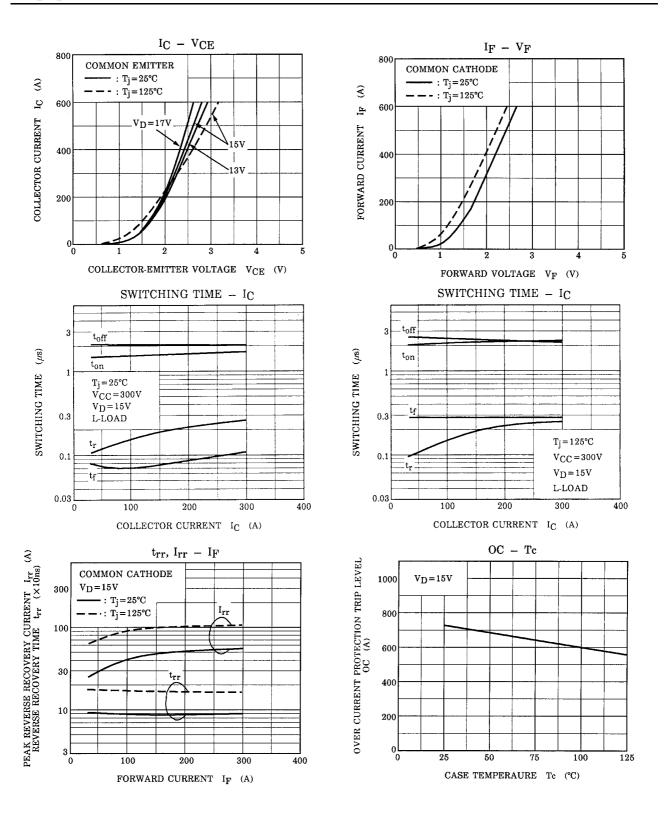
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Control circuit current		I _D	V _D = 15V	_	20	30	mA
Input on signal voltage		V _{IN (on)}	V _D = 15V, I _C = 300mA	0.9	1.1	1.3	V
Fault output current	Protection	I _{FO (on)}	- V _D = 15V	8	10	12	mA
	Normal	I _{FO (off)}		_	_	1	
Over current protection trip level		ОС	V _D = 15V, T _j = 125°C	420	540	_	Α
Short circuit protection trip level		SC	V _D = 15V, T _j = 125°C	630	810	_	Α
Over current cut-off time		t _{off (OC)}	V _D = 15V	_	10	_	μs
Over	Trip level	ОТ	Casa tamananatura	111	118	125	°C
temperature protection	Reset level	OTr	Case temperature	93	100	107	C
Control supply	Trip level	UV		11.3	12.0	12.7	V
under voltage protection	Reset level	UVr	_	11.8	12.5	13.2	
Fault output pulse width		t _{FO}	V _D = 15V	1	2	3	ms

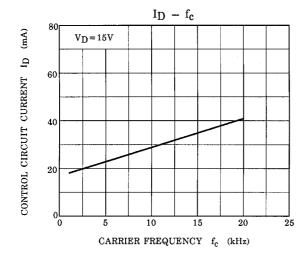
c. Thermal Resistance ($T_j = 25$ °C)

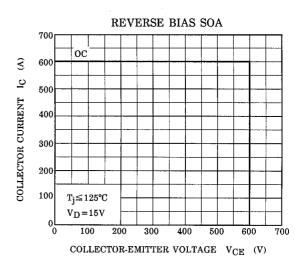
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Junction to case thermal resistance	R _{th (j−c)}	IGBT	_	_	0.104	°C/W
Junction to case thermal resistance		FRD	_	_	0.208	
Case to fin thermal resistance	R _{th (c-f)}	Compound is applied	_	0.05		°C/W

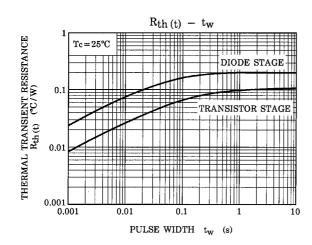
Note 1: Switching time test circuit & timing chart





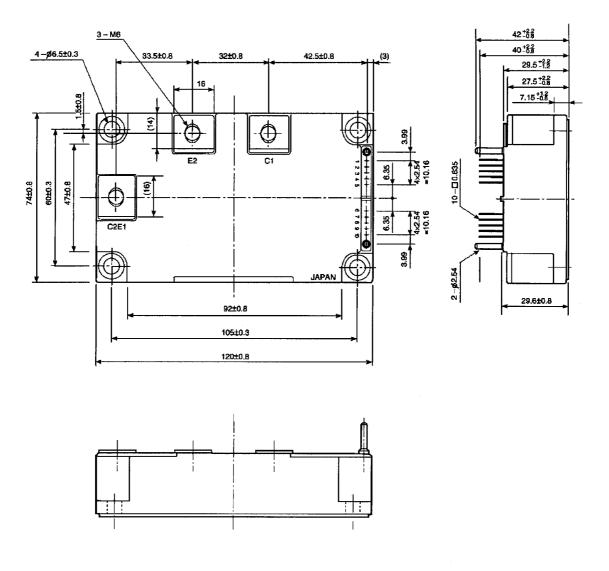






Package Dimensions: TOSHIBA 2-121A1A

Unit: mm



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